

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Tikashi AKATSU *et al.*

Application No:

Group Art Unit:

Filing Date: Concurrently herewith

Examiner:

For: WAFER WITH A RELAXED USEFUL
LAYER AND METHOD OF FORMING THE
WAFER

Attorney Docket No.: 4717-8900

INFORMATION DISCLOSURE STATEMENT

MS PATENT APPLICATION

Commissioner for Patents

P.O. Box 1450

Arlexandria, Virginia 22313-1450

Sir:

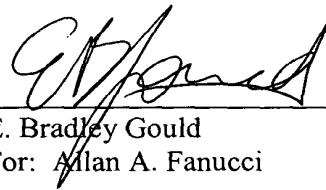
Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed are copies of Nine (9) references listed on the enclosed Form PTO-1449 for the Examiner's review. Also enclosed is a copy of the International Search Report from the corresponding foreign application on which the references were cited.

It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

No fee is believed to be due for the submission of the references. Should any fees be required, however, please charge such fees to Winston & Strawn Deposit Account No. 50-1814. A copy of this sheet is enclosed for accounting purposes.

Respectfully submitted,

Sept. 17, 2003
Date


E. Bradley Gould (Reg. No. 41,792)
For: Allan A. Fanucci (Reg. No. 30,256)

WINSTON & STRAWN
Customer No. 28765

202-371-5771

LIST OF REFERENCES CITED BY APPLICANT Form PTO-1449 <i>(Use several sheets if necessary)</i>				ATTY. DOCKET NO.:	APPLICATION NO.:			
				4717-8900				
				APPLICANT:				
				Tukeshi AKATSU, et al.				
Sheet 1 of 1				FILING DATE:	GROUP:			
U.S. PATENT DOCUMENTS								
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
		US 2002/0185686 A1	12/2002	Christiansen <i>et al.</i>	257	347		
		US 2002/0072130 A1	06/2002	Cheng <i>et al.</i>	438	10		
		US 2001/0003269	06/2001	Wu <i>et al.</i>	117	94		
		6,064,081	05/2000	Robinson	257	183		
		5,461,243	10/1995	Ek <i>et al.</i>	257	190		
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
		EP 0 849 788 A	06/1998	Europe				
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)								
		H. Trinkaus, <i>Strain relaxation mechanism for hydrogen-implanted Si_{1-x}Ge_x/Si(100) heterostructures</i> , 12 June 2000, pp. 3552-54.						
		B. Holländer, <i>Strain relaxation of pseudomorphic Si_{1-x}Ge_x/Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication</i> , 2001, pp. 357-67.						
		B. Holländer, <i>Substrate Engineering by Hydrogen or Helium Implantation for Epitaxial Growth of Lattice Mismatched Si_{1-x}Ge_x Films on Silicon</i> , 2000, pp. 326-29.						
EXAMINER				DATE CONSIDERED				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								